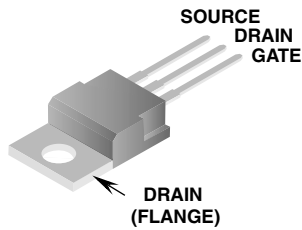


**75A, 80V, 0.010 Ohm, N-Channel,
UltraFET® Power MOSFET**

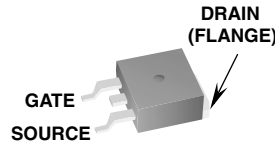
Packaging

JEDEC TO-220AB

JEDEC TO-263AB

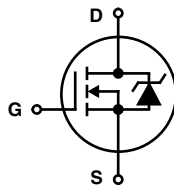


HUFA75545P3



HUFA75545S3S

Symbol



Features

- Ultra Low On-Resistance
 - $r_{DS(ON)} = 0.010\Omega$, $V_{GS} = 10V$
- Simulation Models
 - Temperature Compensated PSPICE® and SABER™ Electrical Models
 - Spice and SABER Thermal Impedance Models
 - www.fairchild.com
- Peak Current vs Pulse Width Curve
- UIS Rating Curve

Ordering Information

PART NUMBER	PACKAGE	BRAND
HUFA75545P3	TO-220AB	75545P
HUFA75545S3S	TO-263AB	75545S

NOTE: When ordering, use the entire part number. Add the suffix T to obtain the TO-263AB variant in tape and reel, e.g., HUFA75545S3ST.

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	HUFA75545P3, HUFA75545S3S	UNITS
Drain to Source Voltage (Note 1)	V_{DSS} 80	V
Drain to Gate Voltage ($R_{GS} = 20k\Omega$) (Note 1)	V_{DGR} 80	V
Gate to Source Voltage	V_{GS} ± 20	V
Drain Current		
Continuous ($T_C = 25^\circ\text{C}$, $V_{GS} = 10V$) (Figure 2)	I_D 75	A
Continuous ($T_C = 100^\circ\text{C}$, $V_{GS} = 10V$) (Figure 2)	I_D 73	A
Pulsed Drain Current	I_{DM} Figure 4	
Pulsed Avalanche Rating	UIS Figure 6	
Power Dissipation	P_D 270	W
Derate Above 25°C	1.8	$W/^\circ\text{C}$
Operating and Storage Temperature	T_J, T_{STG} -55 to 175	$^\circ\text{C}$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s.	T_L 300	$^\circ\text{C}$
Package Body for 10s, See Techbrief TB334	T_{pkg} 260	$^\circ\text{C}$

NOTES:

1. $T_J = 25^\circ\text{C}$ to 150°C .

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: <http://www.aecouncil.com/>

Reliability data can be found at: <http://www.mtp.fairchild.com/automotive.html>.

All Fairchild semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

HUFA75545P3, HUFA75545S3S

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
OFF STATE SPECIFICATIONS							
Drain to Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V (Figure 11)	80	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 75V, V _{GS} = 0V	-	-	1	μA	
		V _{DS} = 70V, V _{GS} = 0V, T _C = 150°C	-	-	250	μA	
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±20V	-	-	±100	nA	
ON STATE SPECIFICATIONS							
Gate to Source Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250μA (Figure 10)	2	-	4	V	
Drain to Source On Resistance	r _{DS(ON)}	I _D = 75A, V _{GS} = 10V (Figure 9)	-	0.0082	0.010	Ω	
THERMAL SPECIFICATIONS							
Thermal Resistance Junction to Case	R _{θJC}	TO-220 and TO-263	-	-	0.55	°C/W	
Thermal Resistance Junction to Ambient	R _{θJA}		-	-	62	°C/W	
SWITCHING SPECIFICATIONS (V _{GS} = 10V)							
Turn-On Time	t _{ON}	V _{DD} = 40V, I _D = 75A V _{GS} = 10V, R _{GS} = 2.5Ω	-	-	210	ns	
Turn-On Delay Time	t _{d(ON)}		-	14	-	ns	
Rise Time	t _r		-	125	-	ns	
Turn-Off Delay Time	t _{d(OFF)}		-	40	-	ns	
Fall Time	t _f		-	90	-	ns	
Turn-Off Time	t _{OFF}		-	-	195	ns	
GATE CHARGE SPECIFICATIONS							
Total Gate Charge	Q _{g(TOT)}	V _{GS} = 0V to 20V	V _{DD} = 40V, I _D = 75A, I _{g(REF)} = 1.0mA (Figure 13)	-	195	235	nC
Gate Charge at 10V	Q _{g(10)}	V _{GS} = 0V to 10V		-	105	125	nC
Threshold Gate Charge	Q _{g(TH)}	V _{GS} = 0V to 2V		-	6.8	8.2	nC
Gate to Source Gate Charge	Q _{gs}			-	15	-	nC
Gate to Drain “Miller” Charge	Q _{gd}			-	43	-	nC
CAPACITANCE SPECIFICATIONS							
Input Capacitance	C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz (Figure 12)	-	3750	-	pF	
Output Capacitance	C _{OSS}		-	1100	-	pF	
Reverse Transfer Capacitance	C _{RSS}		-	350	-	pF	

Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	V_{SD}	$I_{SD} = 75\text{A}$	-	-	1.25	V
		$I_{SD} = 35\text{A}$	-	-	1.00	V
Reverse Recovery Time	t_{rr}	$I_{SD} = 75\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	100	ns
Reverse Recovered Charge	Q_{RR}	$I_{SD} = 75\text{A}$, $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	300	nC

Typical Performance Curves

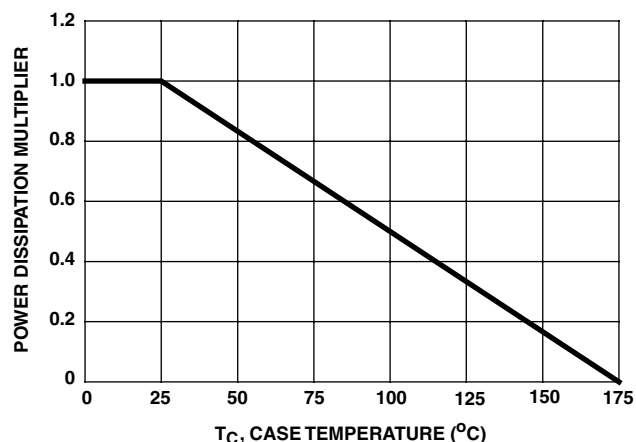


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

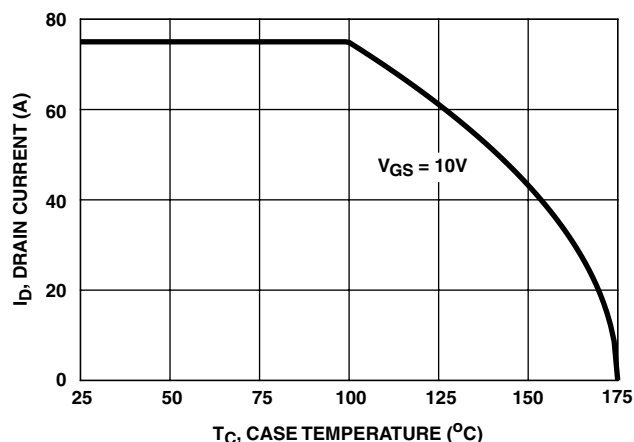


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

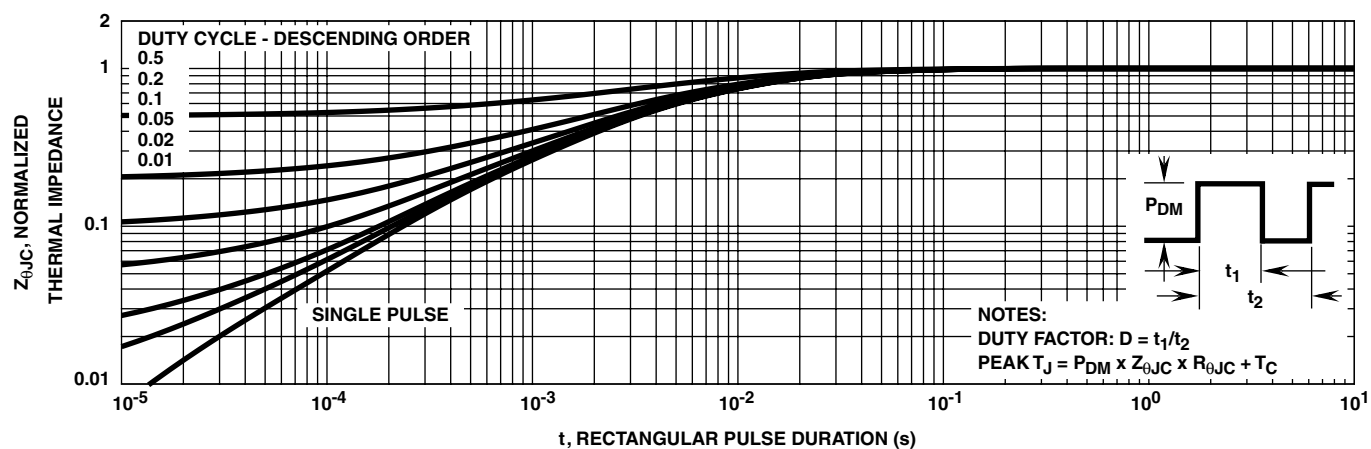


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

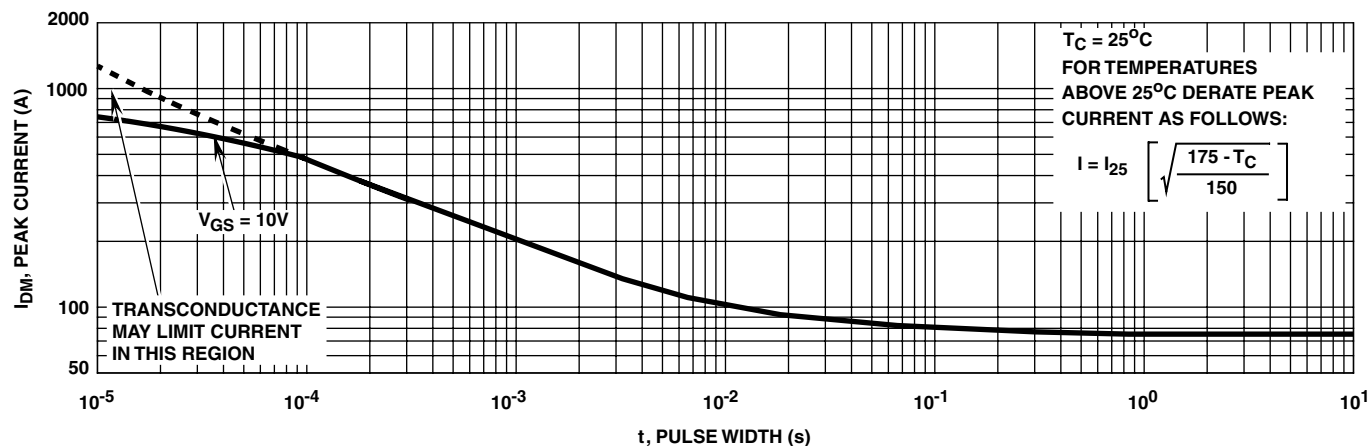


FIGURE 4. PEAK CURRENT CAPABILITY

Typical Performance Curves (Continued)

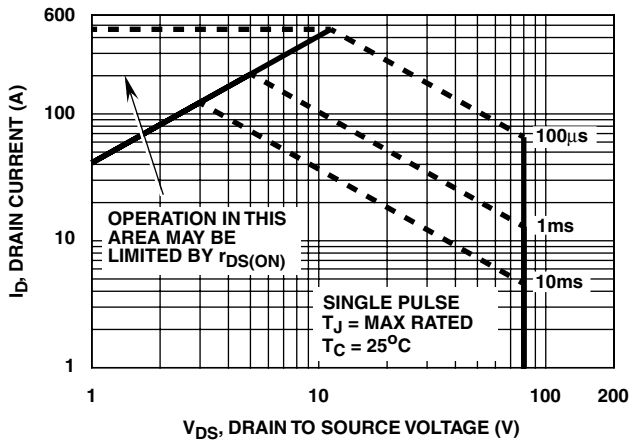
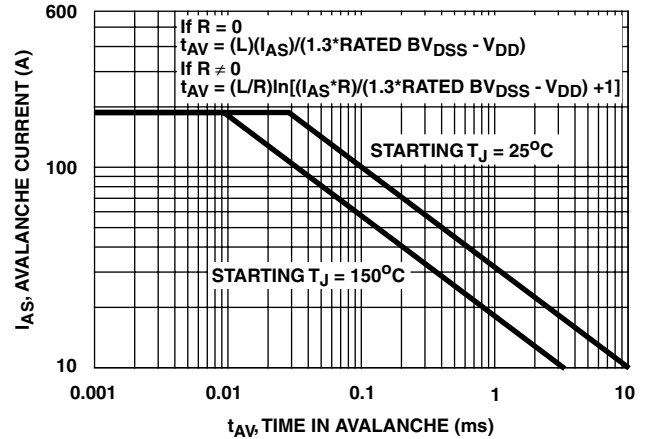


FIGURE 5. FORWARD BIAS SAFE OPERATING AREA



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

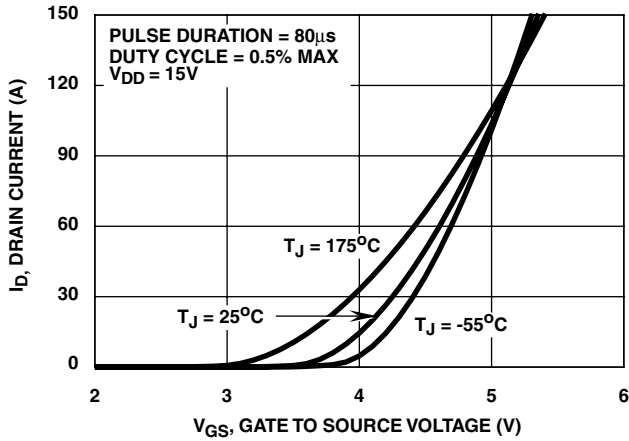


FIGURE 7. TRANSFER CHARACTERISTICS

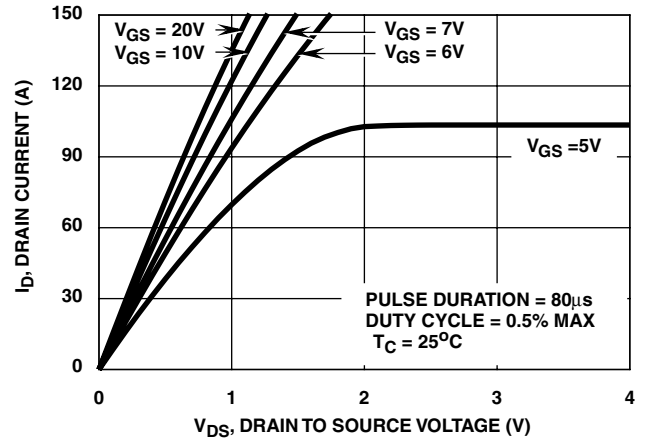


FIGURE 8. SATURATION CHARACTERISTICS

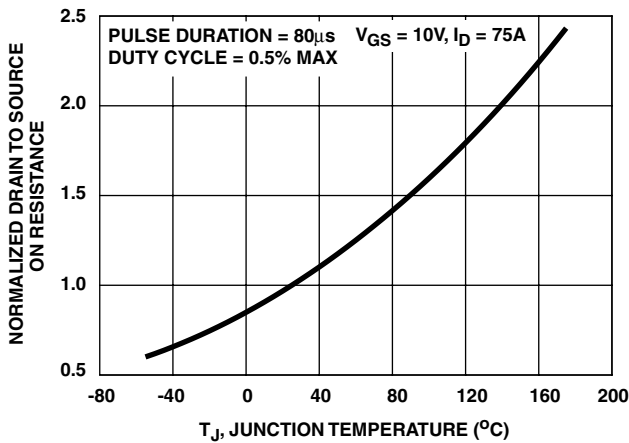


FIGURE 9. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs JUNCTION TEMPERATURE

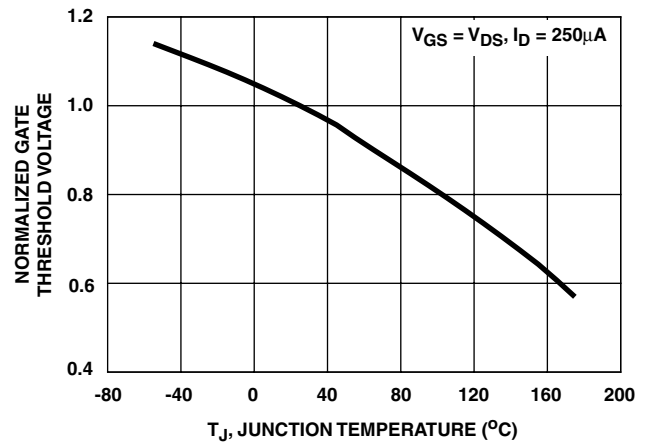


FIGURE 10. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

Typical Performance Curves (Continued)

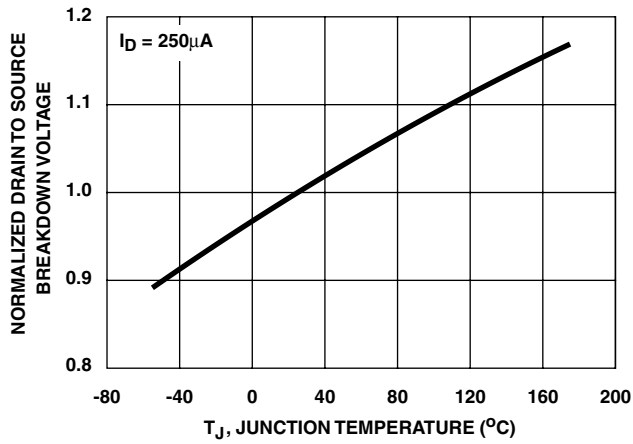


FIGURE 11. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

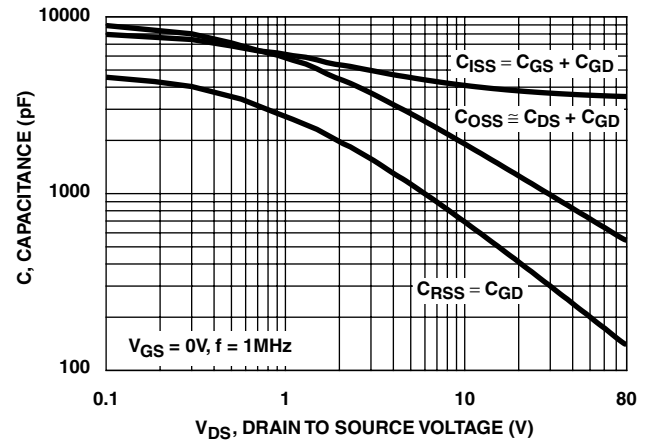
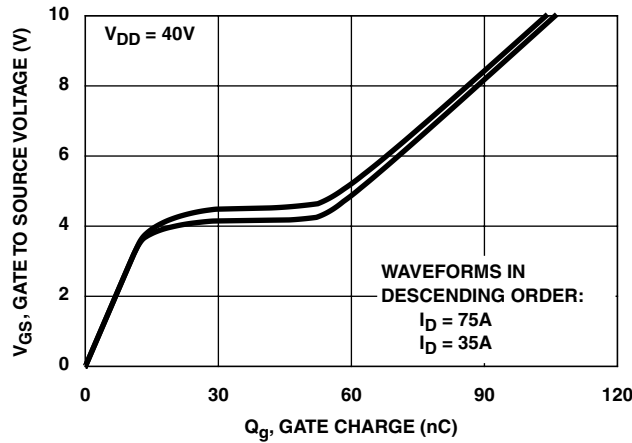


FIGURE 12. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 13. GATE CHARGE WAVEFORMS FOR CONSTANT GATE CURRENT

Test Circuits and Waveforms

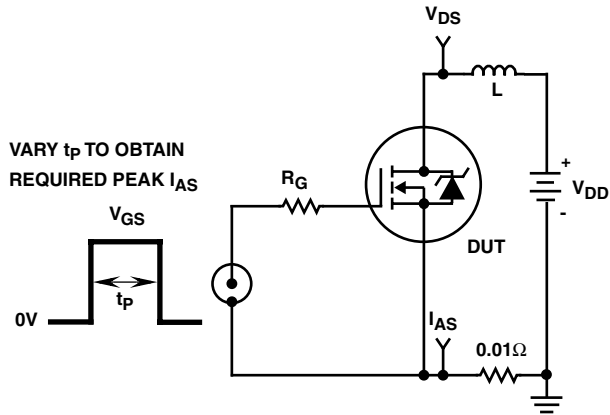


FIGURE 14. UNCLAMPED ENERGY TEST CIRCUIT

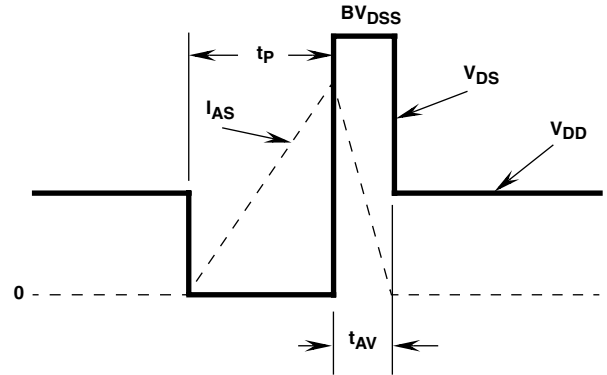


FIGURE 15. UNCLAMPED ENERGY WAVEFORMS

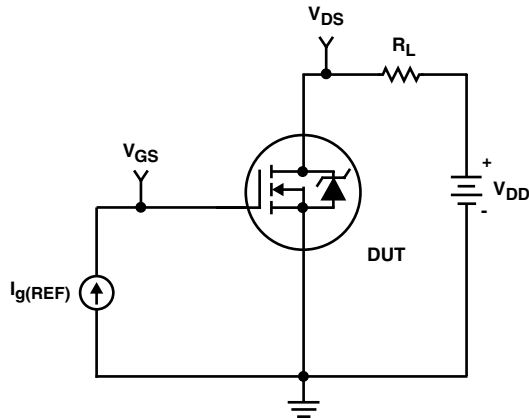


FIGURE 16. GATE CHARGE TEST CIRCUIT

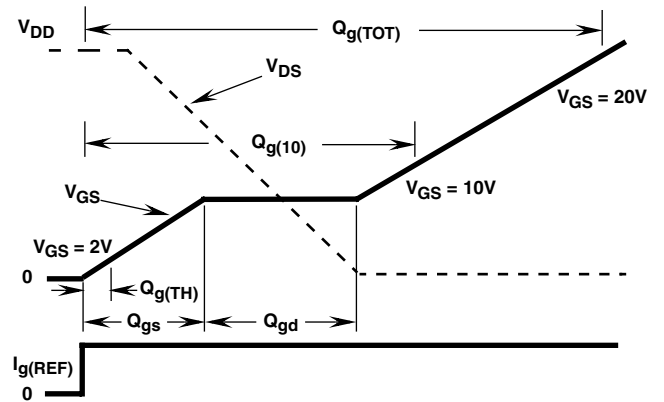


FIGURE 17. GATE CHARGE WAVEFORMS

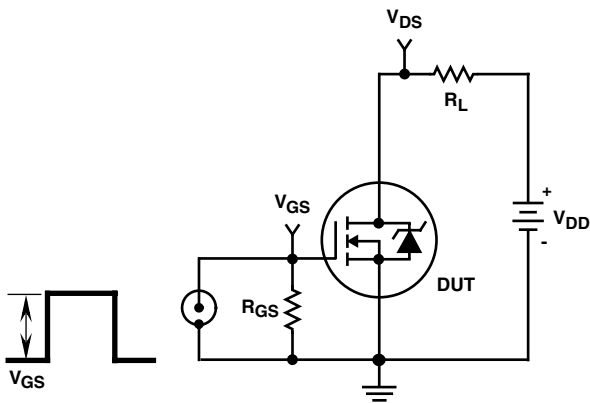


FIGURE 18. SWITCHING TIME TEST CIRCUIT

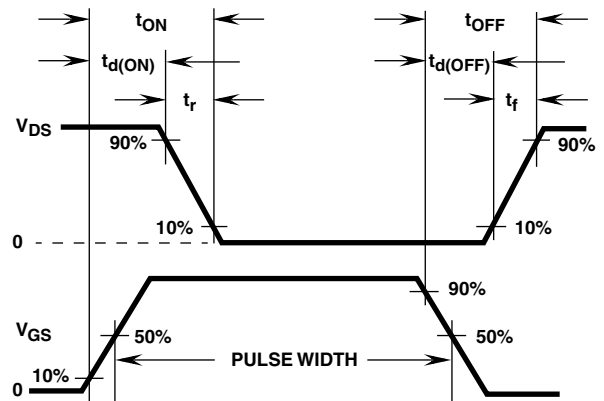
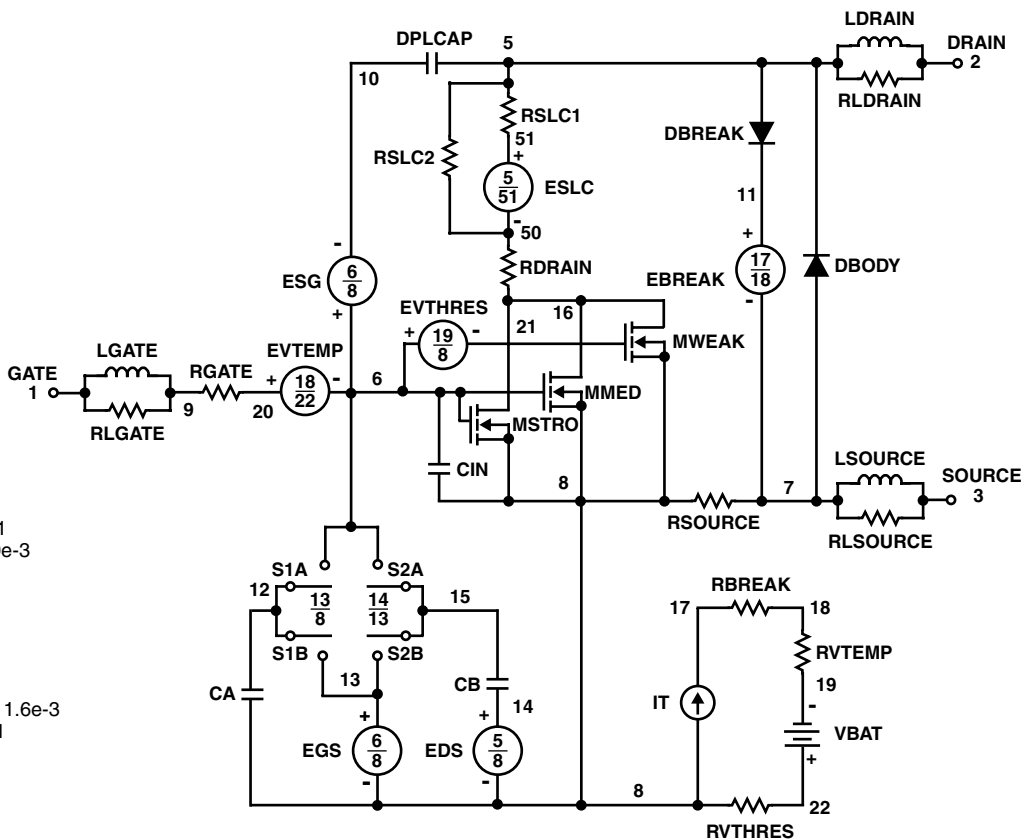


FIGURE 19. SWITCHING TIME WAVEFORM



SPICE Thermal Model

REV 21 May 1999

HUFA75545T

CTHERM1 th 6 6.4e-3
 CHERM2 6 5 3.0e-2
 CHERM3 5 4 1.4e-2
 CHERM4 4 3 1.6e-2
 CHERM5 3 2 5.5e-2
 CHERM6 2 tl 1.5

RHERM1 th 6 3.2e-3
 RHERM2 6 5 8.1e-3
 RHERM3 5 4 2.3e-2
 RHERM4 4 3 1.3e-1
 RHERM5 3 2 1.8e-1
 RHERM6 2 tl 3.8e-2

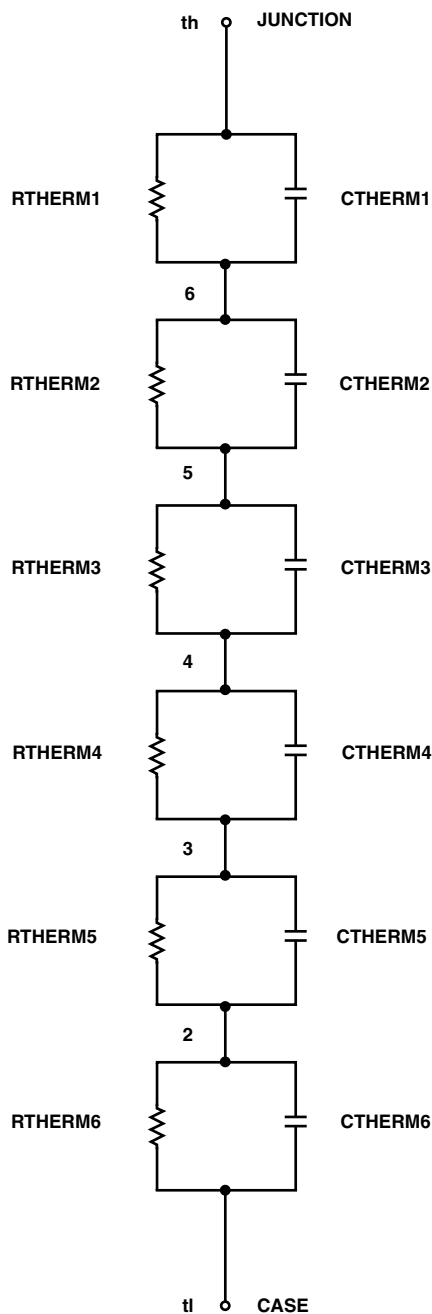
SABER Thermal Model

SABER thermal model HUFA75545T

template thermal_model th tl
 thermal_c th, tl

```
{
    ctherm.therm1 th 6 = 6.4e-3
    ctherm.therm2 6 5 = 3.0e-2
    ctherm.therm3 5 4 = 1.4e-2
    ctherm.therm4 4 3 = 1.6e-2
    ctherm.therm5 3 2 = 5.5e-2
    ctherm.therm6 2 tl = 1.5
}
```

```
rtherm.rtherm1 th 6 = 3.2e-3
rtherm.rtherm2 6 5 = 8.1e-3
rtherm.rtherm3 5 4 = 2.3e-2
rtherm.rtherm4 4 3 = 1.3e-1
rtherm.rtherm5 3 2 = 1.8e-1
rtherm.rtherm6 2 tl = 3.8e-2
}
```



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CROSSVOLT TM	GlobalOptoisolator TM	POP TM	SuperSOT TM -3	
DenseTrench TM	GTO TM	Power247 TM	SuperSOT TM -6	
DOME TM	HiSeC TM	PowerTrench [®]	SuperSOT TM -8	
EcoSPARK TM	ISOPLANAR TM	QFET TM	SyncFET TM	
E ² CMOS TM	LittleFET TM	QS TM	TinyLogic TM	
EnSigna TM	MicroFET TM	QT Optoelectronics TM	TruTranslation TM	
FACT TM	MicroPak TM	Quiet Series TM	UHC TM	
FACT Quiet Series TM	MICROWIRE TM	SILENT SWITCHER [®]	UltraFET [®]	

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